SUB D1 C1

2. (Amended) A method of forming a metal-comprising mass for a semiconductor construction, comprising:

providing a semiconductor substrate;

providing one or more metallo-organic precursors proximate the substrate, at least one of the one or more precursors not comprising platinum;

exposing the one or more precursors to a reducing atmosphere to release metal from the one or more precursors;

depositing the released metal over the semiconductor substrate to form a metal-comprising mass on the semiconductor substrate; wherein the substrate comprises an upper surface consisting of one or more of TiN, elemental Ti, WN, elemental W, TaN and elemental Ta; and the upper surface is exposed to the reducing atmosphere during formation of the metal-comprising mass; and

patterning the metal-containing mass into a rectangular block.

NE

4. (Unchanged) The method of claim 2 wherein the metal-comprising mass is formed physically against the upper surface of the substrate.

C2 SUB D1

13. (Amended) The method of claim 2 wherein the reducing atmosphere comprises plasma-activated hydrogen.

C3

14. (Amended) The method of claim 2 wherein the reducing atmosphere comprises H_2.

42. (Unchanged) The method of claim 2 wherein th upper surfac consists of TiN.

NE

43. (Unchanged) The method of claim 2 wherein the upper surface consists of elemental Ti.

44. (Unchanged) The method of claim 2 wherein the upper surface consists of WN.

45. (Unchanged) The method of claim 2 wherein the upper surface consists of elemental W.

NE

46. (Unchanged) The method of claim 2 wherein the upper surface consists of TaN.

47. (Unchanged) The method of claim 2 wherein the upper surface consists of elemental Ta.